





SECONDARY ION MASS SPECTROMETRY Applications in Materials Characterization

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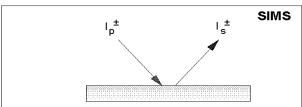




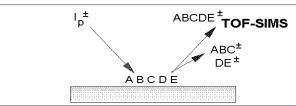
Secondary Ions Mass Spectrometry

- Basic principles
- Instrument design
- Examples of applications in materials characterization

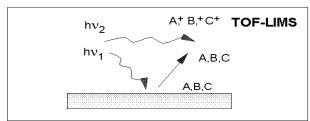




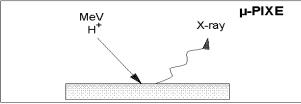
Operated in a dynamic SIMS mode, an energetic primary ion beam is used to sputter atoms from the sample surface. Secondary ions emitted are mass analyzed in electrostatic magnetic sector instrument. Very high sensitivity and quantitative analysis are key features. Depth profiling and imaging capabilities.



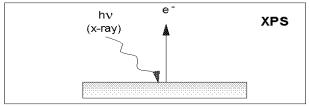
TOF-SIMS generally operates in a static SIMS mode whereby the top monolayers of the sample surface are analyzed. A pulsed ion beam is used and secondary ions emitted from compounds and molecules are mass analyzed and imaged.



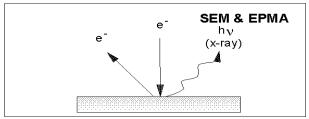
A focused laser beam ablates neutral particles from the sample surface that are indiscriminately ionized by a second powerful laser source using the process of nonresonant multiphoton ionization (NRMPI). Surface analysis of inorganic species with high elemental and surface sensitivity.



A high energy proton beam is focused on a mineral particle to generate characteristic X-rays for elemental detection. Simultaneous multielemental detection and mapping of trace elements.



When the surface of a sample is excited with X-rays, high-resolution energy analysis of photoelectrons emitted from atoms near the surface can be used to characterize a variety of inorganic and organic materials. Chemical bonding information may be determined from the chemical shift of atomic transitions.



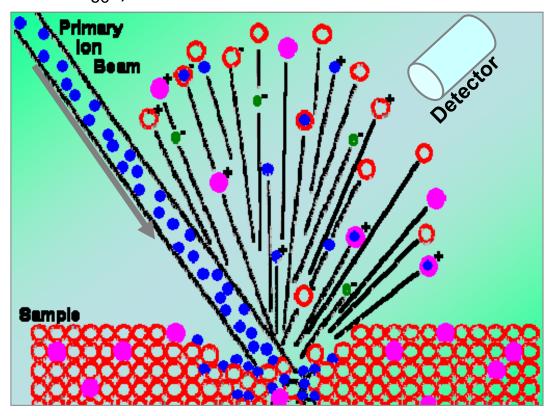
. A finely focused electron beam is rastered over the sample's surface from which an image is formed from the particles produced (e.g. secondary/backscattered electron and photon emission). Combined with energy dispersive X-ray (EDX) spectroscopy elemental quantification is possible. Wavelength dispersive X-ray (WDX) spectroscopy offers improved sensitivity.



Ion beam based micro-beam analytical techniques

Collisional ionization

Primary ion beam based SIMS is a method of analyzing the mass/charge ratio of ionized particles produced from the sample upon bombardment of an energetic (25 keV) primary ion beam (Bi⁺, Cs^+ , C_{60}^+).



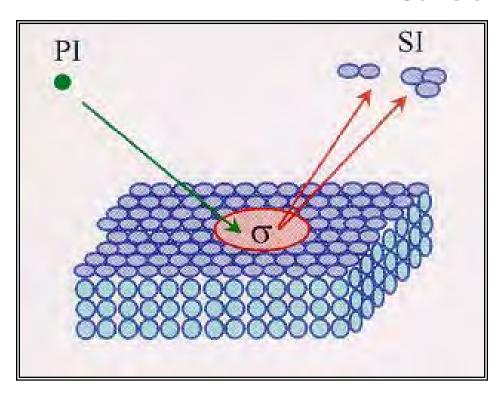
Neutral particles

lons

Electrons



Ion beam based micro-beam analytical techniques Collisional ionization



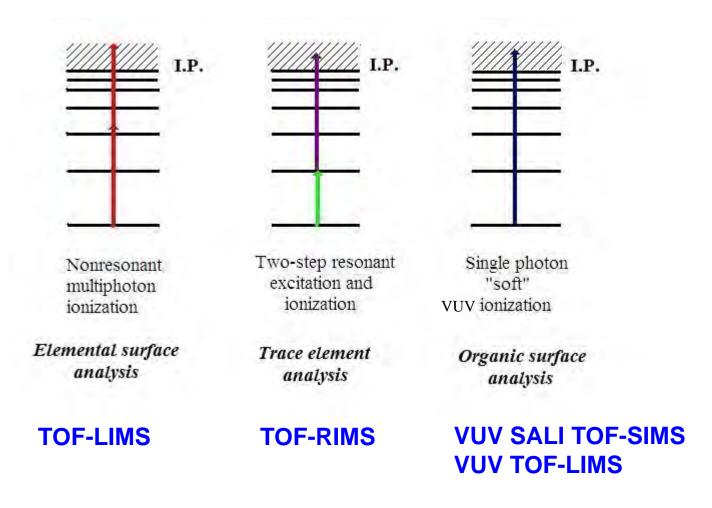
The SIMS process is <u>destructive</u> –
 one sacrifices the surface particles
 that are analyzed by the mass
 spectrometer.

- Static SIMS (TOF SIMS): secondary ion emission from damaged areas is negligible. Analytical depth is limited to top monolayers.
- Dynamic SIMS: truly destructive, high primary ion beam fluence.



Laser based micro-beam analytical techniques

Optical ionization





Instrument Design

Key performance characteristics

- Destructive/non-destructive analysis
- Elemental/ molecular analysis
- Surface sensitivity/depth profiling
- Imaging capacity
- Mass resolution
- Detection limits

Key factors

- Primary ionization source
- Mass spectrometer type



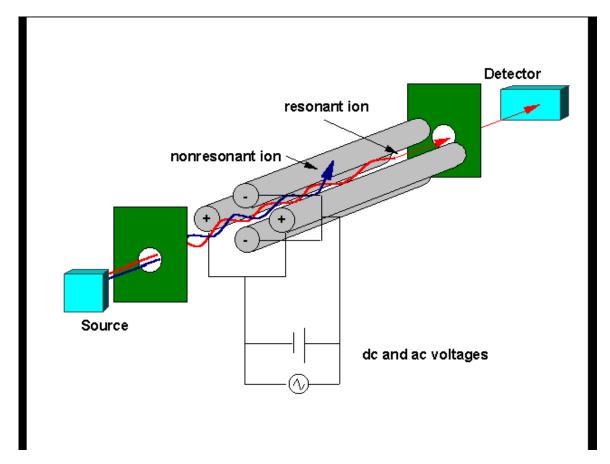
Instrument Design

Choice of mass spectrometer type

- Quadrupole type mass spectrometer
- Magnetic sector type mass spectrometer
- Time-of-flight type mass spectrometer



Quadrupole Mass Spectrometer



Mass spectrometers separate ions according to their mass-to-charge ratio (m/z)

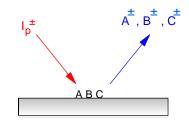
Features:

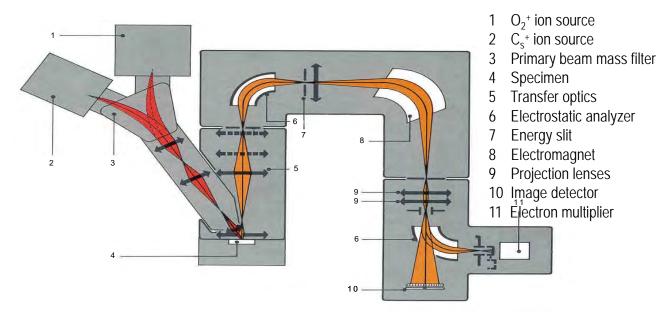
- Good reproducibility
- Relatively small and low cost systems
- Limited resolution and ion transmission in the range of 10⁻³ 10⁻⁴
- Benchtop GC/MS and LC/MS systems
- Triple quadrupole MS systems



Dynamic SIMS

Magnetic sector mass spectrometer CAMECA SIMS instrument





High performance mass spectrometer

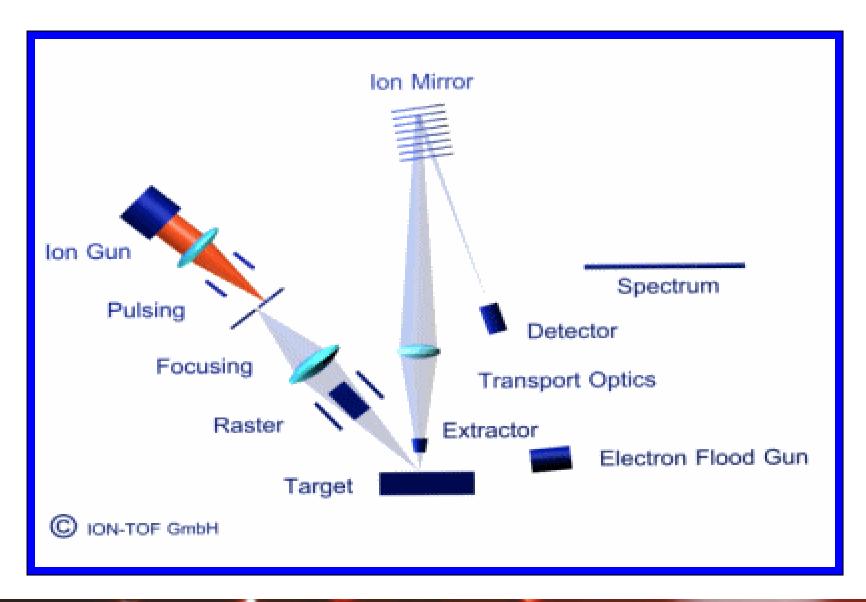
- Very high reproducibility
- **■** Best quantitative performance
- High mass resolution
- High sensitivity
- High dynamic range
- Imaging capabilities; 1µm lateral resolution

D-SIMS System Capabilities:

- Elemental and isotopic survey analysis covering the entire periodic table
- Quantitative microanalysis;MDL100 ppb
- **■** Elemental depth profiling
- **■** Imaging

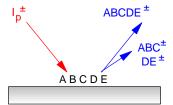


Time-of-Flight Mass Spectrometer TOF-MS



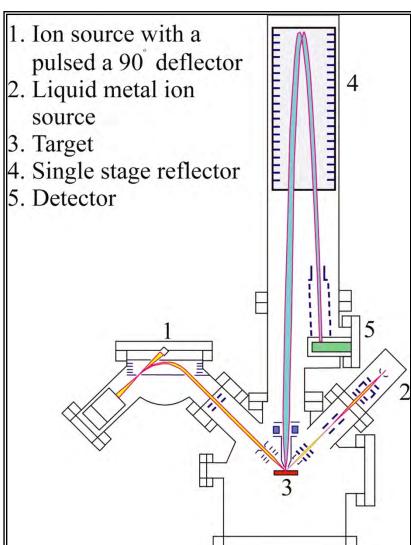


Time-of-Flight Secondary Ions Mass Spectrometry (TOF SIMS)





ION TOF IV TOF SIMS instrument
This mass spectrometer is able to
analyze an unlimited mass range with
high sensitivity and parallel detection
of all secondary ions collected by the
mass spectrometer.





TOF-SIMS Technique

Last generation instrument

ION TOF IV TOF-SIMS equipped with Cs, C₆₀ and Bi ion cluster guns

STATIC SIMS mode of operation System capabilities:

- Non destructive elemental and molecular compound analysis
- High mass range (above 10,000 Daltons) and high mass resolution: M/ΔM >2,000-10,000
- Detection limits in the low ppm/ppb range
- Imaging with spatial resolution down to 0.3µm
- Depth profiling with depth resolution of less than 10A
- Retrospective analysis

Relevance:

Benchmark technique for elemental and molecular surface analysis



Secondary Ion Mass Spectrometry Techniques

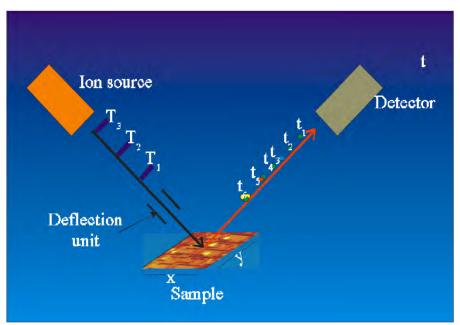
Primary source	Mass Spectrometer	Technique	Area of application			
			Surface analysis	Depth profiling	Trace element analysis	Imaging
VIS/UV laser	TOF MS	TOF-LIMS	√ Elemental		V	
	Quadrupole MS	LA ICPMS			Elemental	Elemental
Tunable laser	TOF MS	TOF-RIMS			√ Elemental	
VUV laser	TOF MS	VUV TOF-LIMS	√ Molecular			
Pulsed Cs, O ₂ ion sources	TOF MS	TOF-SIMS	√ Elemental	V		√ Elemental
Ion cluster sources: Bi ⁿ⁺ ,Au ⁿ⁺ ,C60	TOF MS	TOF-SIMS	√ Elemental & Molecular	V		√ Elemental & Molecular
DC Cs, O ₂ ion sources	Magnetic Sector MS	Dynamic SIMS		√	√ Elemental	√ Elemental



TOF-SIMS Retrospective Analysis

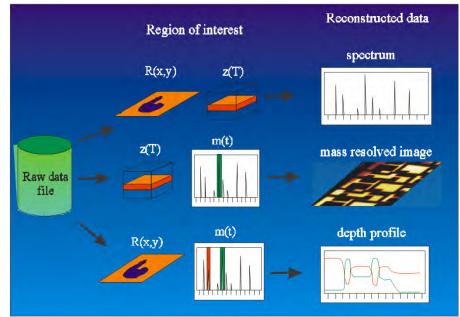
Acquisition of raw data

Storage: time-of-flight (t), position (x,y) and measurement time (T) for each SI

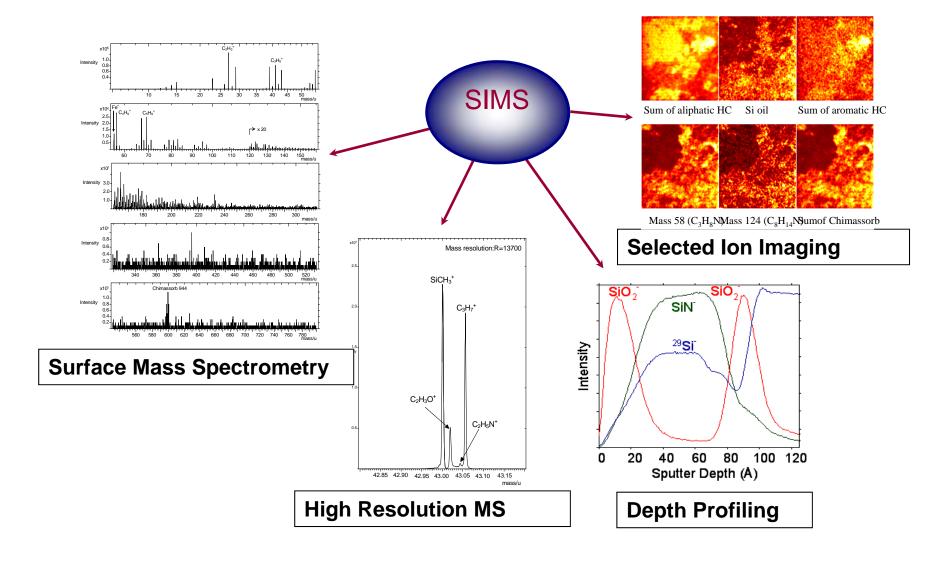


Retrospective Analysis

4D raw data file with (x,y,z,m) for each SI detected allows to reconstruct spectra, profiles and images

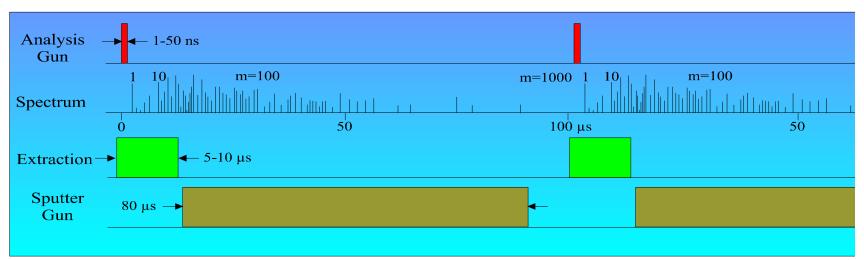








Dual beam depth profiling

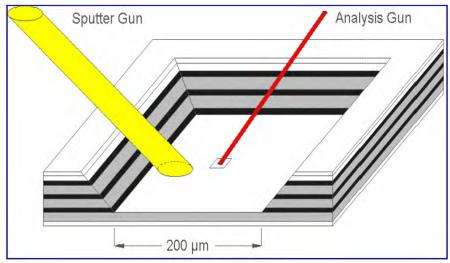


Analysis:

- high energy beam
- ⇒ high lateral resolution

Sputtering:

- low energy beam
- free choice of ion species
- ⇒ high depth resolution

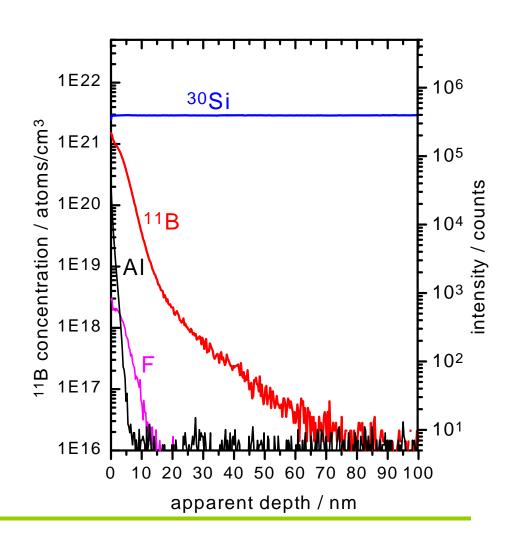




Ultra Shallow Implants

Example: BF₂ Implant in Silicon

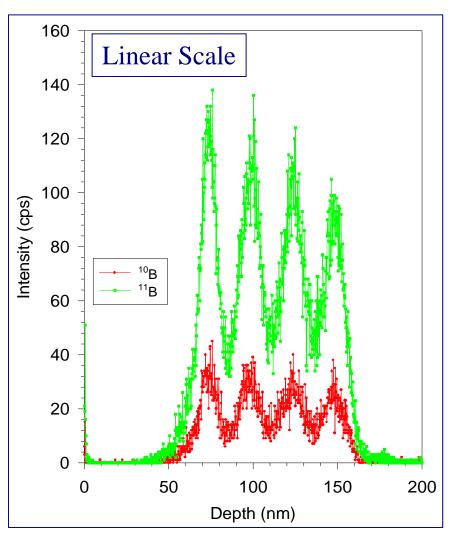
- High Sensitivity (detection limit ¹¹B: 1E16 at./cm³)
- High Depth Resolution (decay length Al: 0.77 nm)
- Parallel Mass Detection (contaminant screening)





Ultra-Shallow Depth Profiles of B implants in Si wafer

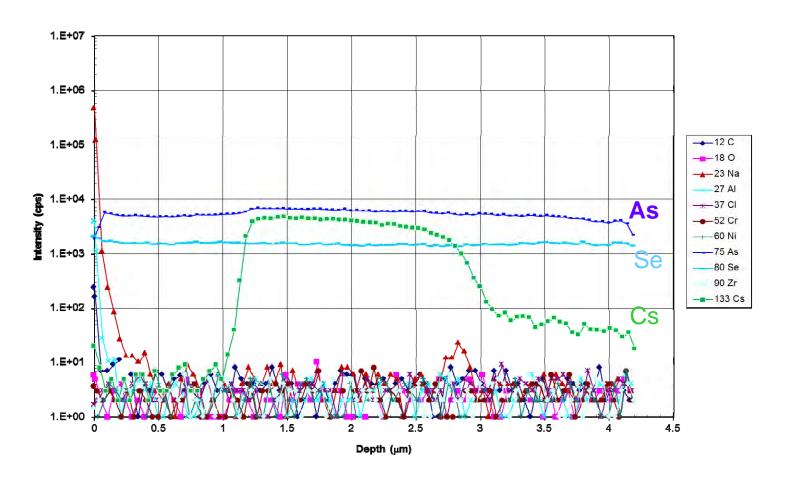
$$4 \times (100A 5 \times 10^{19} B/cm^3)$$





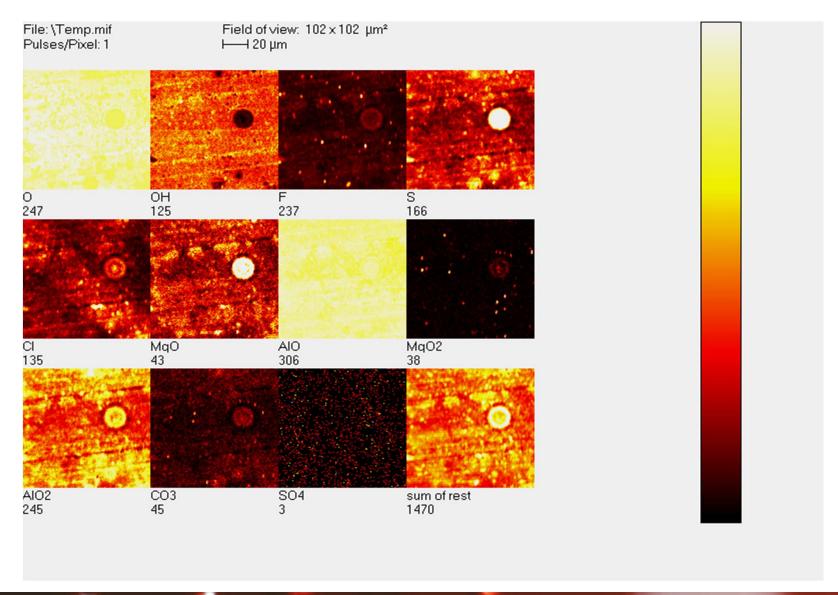
D-SIMS depth profile of Cs in Arsenic rich layer used in X-ray detector

Glass coating sample intensity vs. Depth



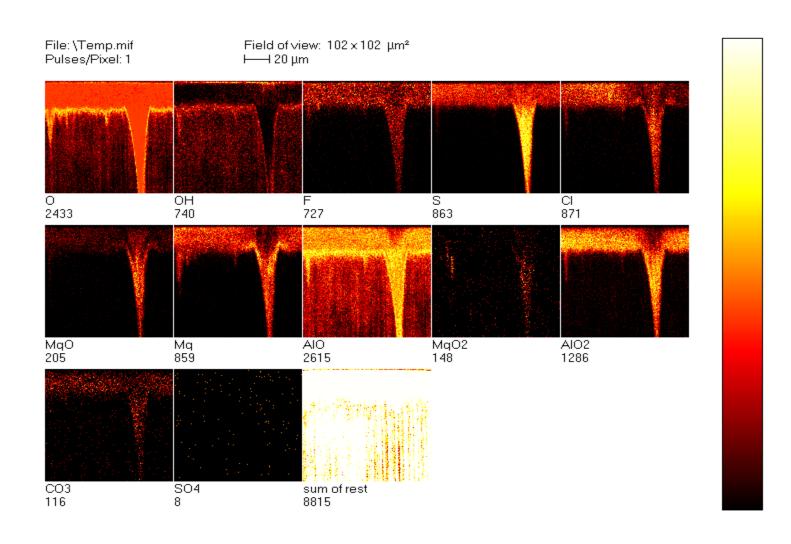


Corrosion on Al sample, Plan View





3-D Cross Section Reconstructed from Raw Data





- Steam Generator tubing from four Canadian nuclear stations examined (in service from 1.5 to 26 years).
- Steam Generator tubing may experience measurable aging (change in composition/microstructure) after many years of service.
- Precipitation of some elements had occurred.

Area\Tube ID	D4 SG3 R54C76 2 Yrs of Service	D4 SG1 R49C61 10 Yrs of Service	G2 SG3 X69Y54 25.5 Yrs of Service	PLGS SG3 R32C65 26.8 Yrs of Service
OD Edge				
ID Edge				
Mid-Section				

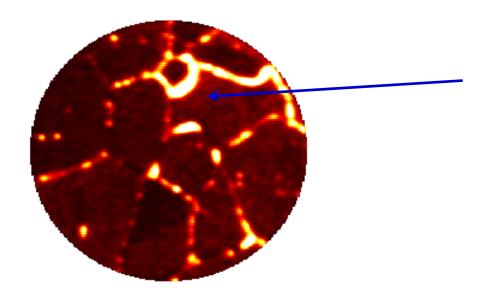
• Increased B (as BO) precipitation as a function of # of years in service.



- Impurity precipitation at the metal grain boundaries can result in preferential corrosion along the grain boundaries.
- Intergranular attack (IGA) was observed on Alloy 800 steam generator (SG) tubing removed from service in a nuclear power station.
- Alloy 800 composition: 30-35%Ni, 19-23% Cr, 39.5% Fe (max), 0.10 C (max), 0.15-0.6 Al, 0.15-0.6 Ti, 0.3-1.2 Al+Ti (max).
- B is an impurity present at levels well below that of the major alloying elements.
- Secondary Ion Mass Spectrometry (SIMS) imaging was employed to determine grain boundary precipitation:
 - SIMS can detect all elements from hydrogen to uranium.
 - Dynamic SIMS has very low detection limits, of the order of ppm and even ppb for some elements.
 - SIMS depth profiling can be used to determine the composition distribution within layers up to 10-20 µm deep in a reasonable period of analysis time (4-5 hours).

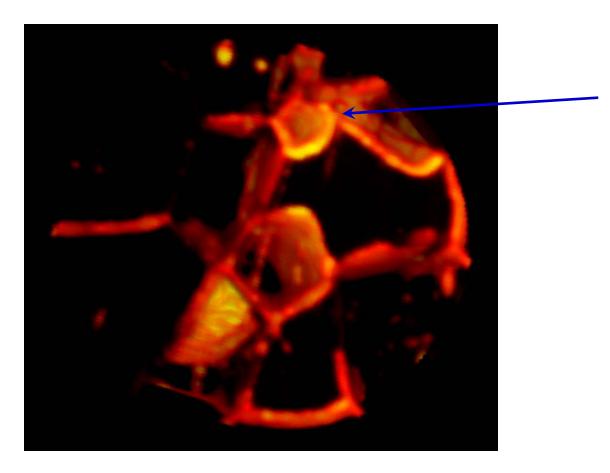


Intergranular attack (IGA)



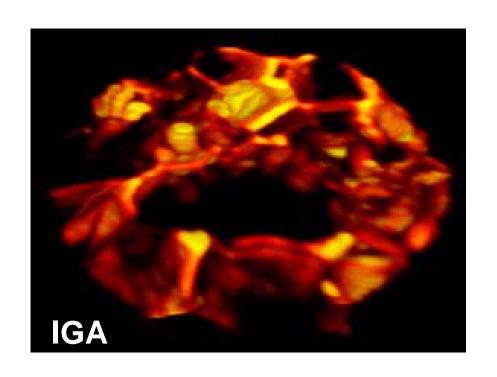
- One slice of ²⁷BO image.
- Precipitation of B along the grain boundaries can be seen in this image.

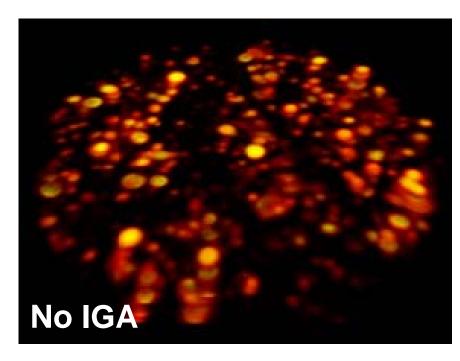




- 3D image of the same volume slide shown in the previous slide.
- ²⁷BO precipitation along the grain boundaries can be clearly seen.
- The grain pointed by the blue arrow is the same one as in the previous slide.





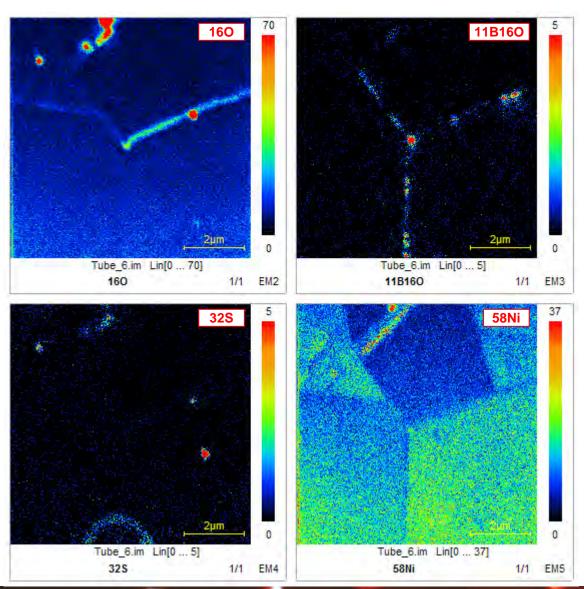


 3D images of ²⁷BO distribution at the grain boundaries on regions exhibiting IGA and no IGA.



Nano-SIMS Imaging

Nano-SIMS can image features as small as 50 nm

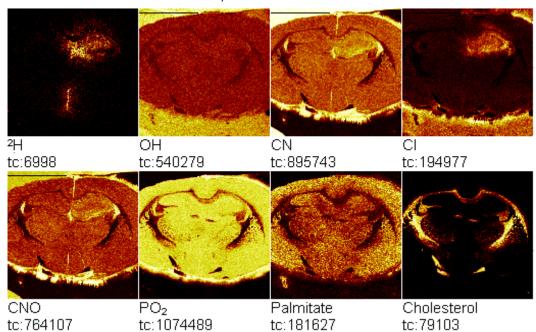


- Negative secondary ions, Cs+ primary ion source
- ⁵⁸Ni describes the grain structure
- ²⁷BO, ¹⁶O and ³²S are corrosion related impurities.

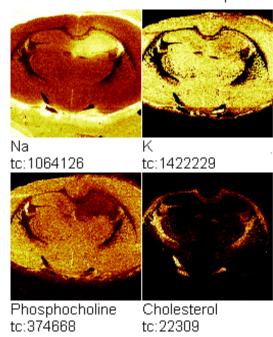


Ion images of a sectioned rat brain

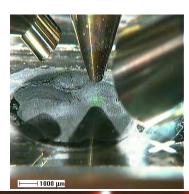
Field of view: $12000.0 \times 12000.0 \, \mu m^2$



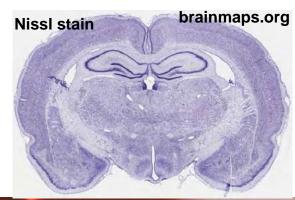
Field of view: 12000.0 x 12000.0 µm²



Optical image showing the setup

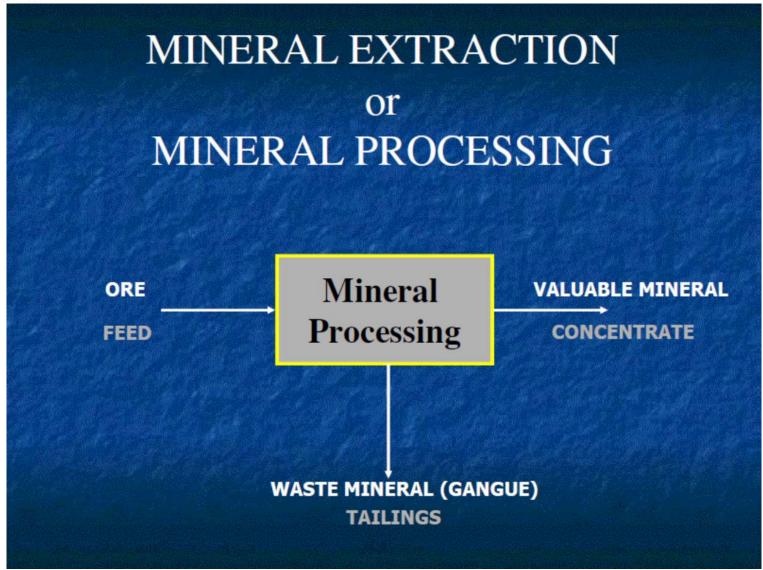


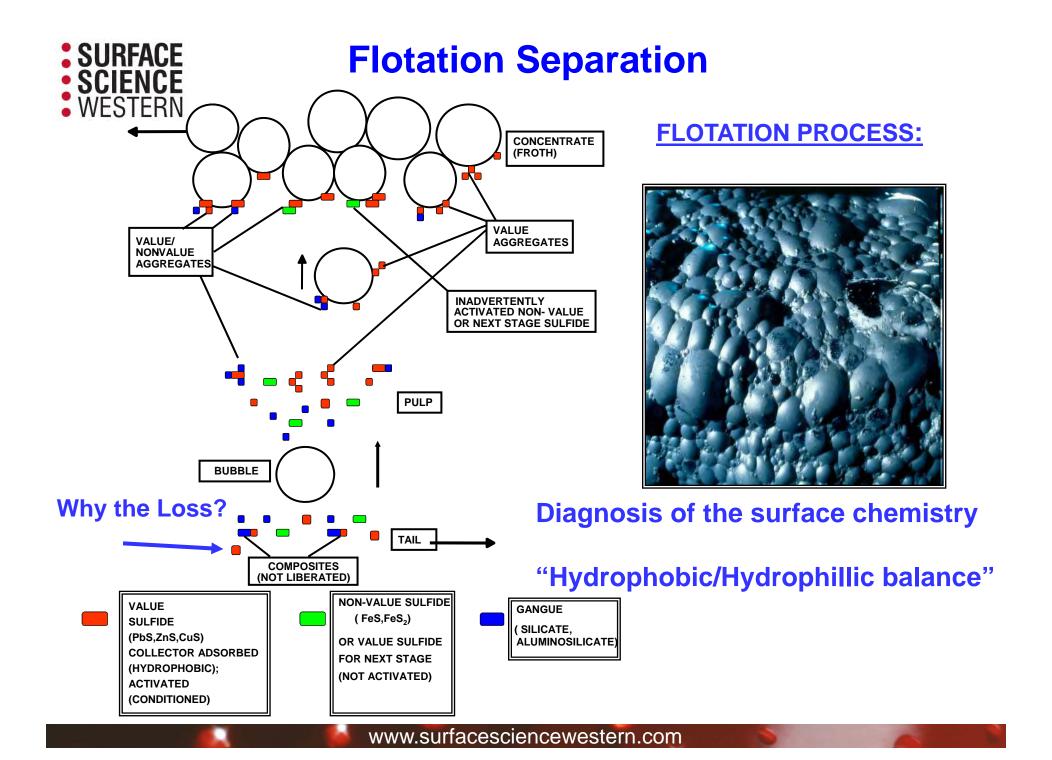
Nissl stain with Cresyl Violet Staining Nissl body (ER) with aniline containing dye





Froth flotation





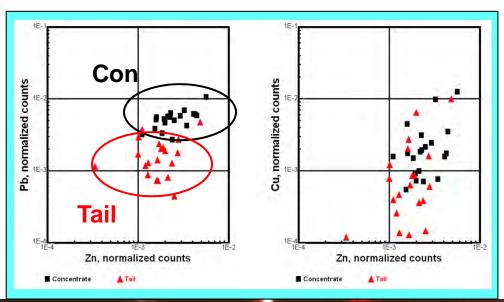
SURFACE Sphalerite in Cu con Tail 207pb 206.0 207pb 207pb

Surface analysis applied to mineral processing: Case #1

Flotation products Inadvertent activation

ToF-SIMS Spectra:

 Pb on surface of sphalerite grain in concentrate and tail samples



Concentrate versus tail scatter plots showing the distribution for Pb and Cu versus Zn on sphalerite surfaces



Gold deportment studies and optimized gold recovery process by SIMS

Facts:

- Very high capital cost in developing of a gold mine: x\$100millions
- Typical gold content in a commercially viable gold deposit: 1-2g/t
- Projected gold recovery : >85%

Objectives:

- To determine all forms and carriers of Au in the ore sample
- Establishing complete and quantitative Au mineralogical balances

 Identification of specific causes for gold losses in the process stream products

Relevance:

- Process mineralogical mapping
- Process selection and optimization



Dynamic SIMS applications in gold deportment studies

<u>Information derived from D-SIMS analysis:</u>

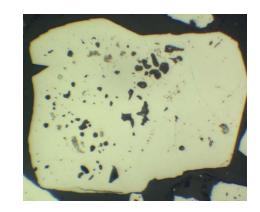
- Characterization of the carriers and forms of sub-microscopic (invisible) gold:
 - i) quantitative analysis
 - ii) forms of sub-microscopic gold: colloidal type and solid solution type gold
 - iii) imaging of the sub-microscopic gold distribution
- Establishing complete and quantitative Au mineralogical balances
- Identification of specific causes for gold losses in the process stream products

Relevance:

- Benchmark technique for analysis of sub-microscopic gold
- Effectively addresses the analytical gap between the electron microprobe (MDL≈200ppm) and bulk analytical techniques (MDL≈low ppb)



Sub-microscopic gold

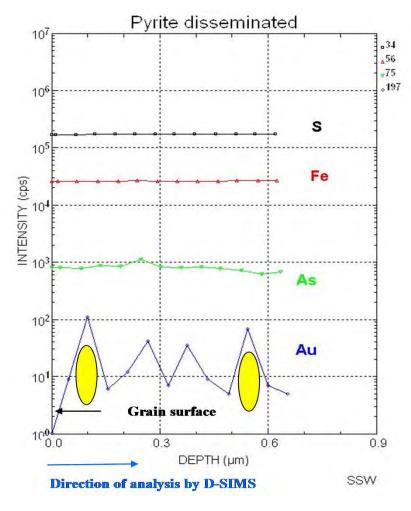


Pyrite (FeS₂)
Common carrier of sub-microscopic gold

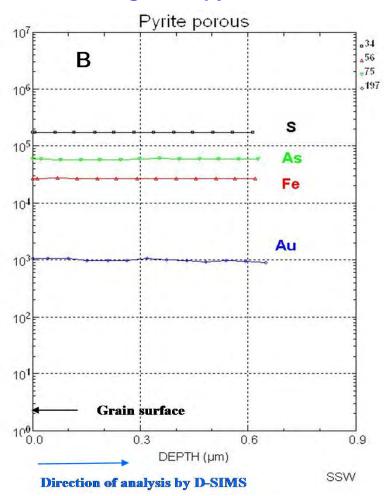
- The sub-microscopic gold is refractory gold, i.e it is locked within the crystalline structure of the mineral phase (most often in sulphide minerals) and it can not be directly released by the cyanide leach process
- **■**Two forms of "invisible" sub-microscopic gold:
 - i) solid solution within the sulphide mineral matrix
 - ii) colloidal size: finely disseminated colloidal size gold particles (<0.5µm)
- Refractory gold ores are becoming the most common gold ore deposits and they need a special treatment in order release the sub-microscopic gold



Colloidal size sub-microscopic gold in pyrite

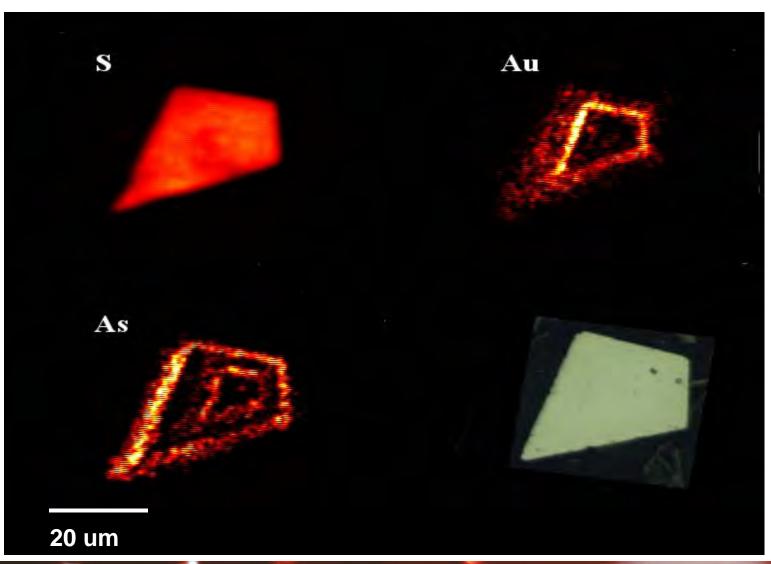


Solid solution type sub-microscopic gold in pyrite

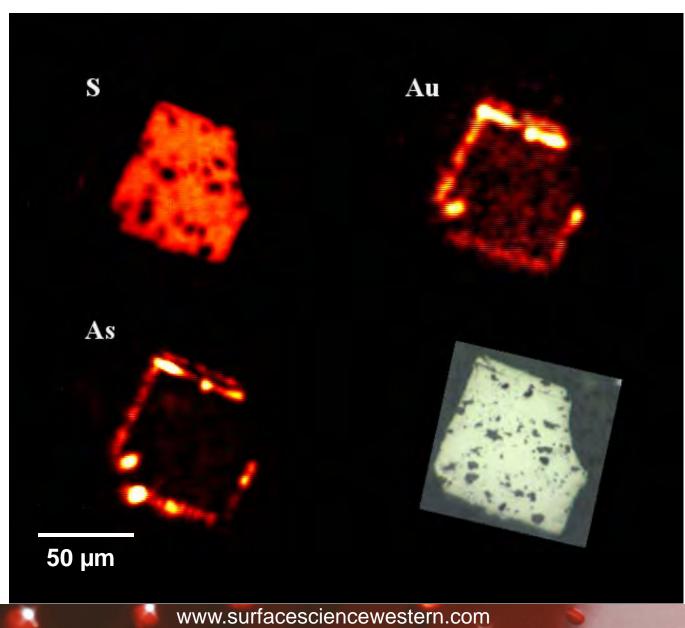




Dynamic SIMS images of gold and arsenic distribution in pyrite

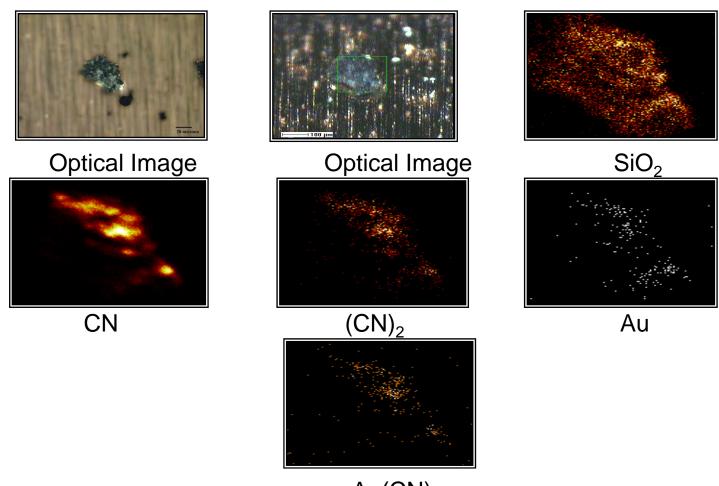








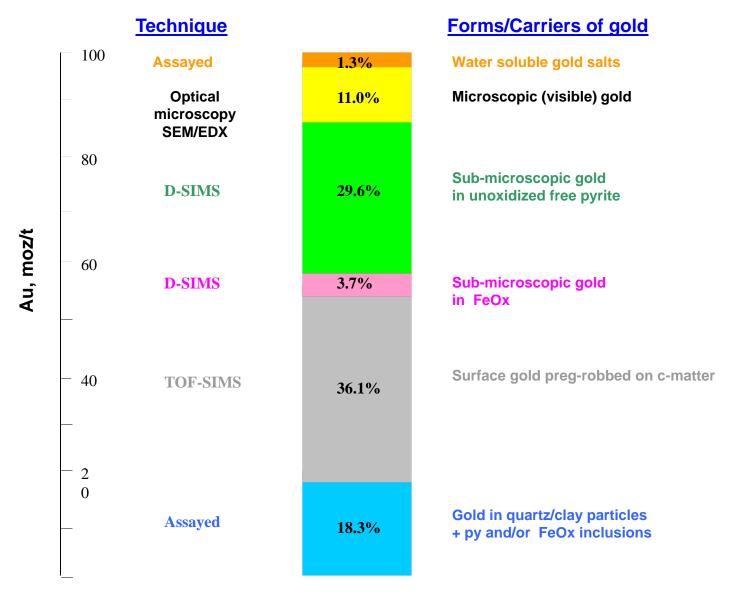
SURFACE Optical images along with TOF-SIMS elemental and compositional SCIENCE maps for disseminated TCM grain from CIL residue



 $Au(CN)_2$ Calculated Au concentration based on Au and $Au(CN)_2$ components = 105 ppm



Gold deportment in CIL residue sample





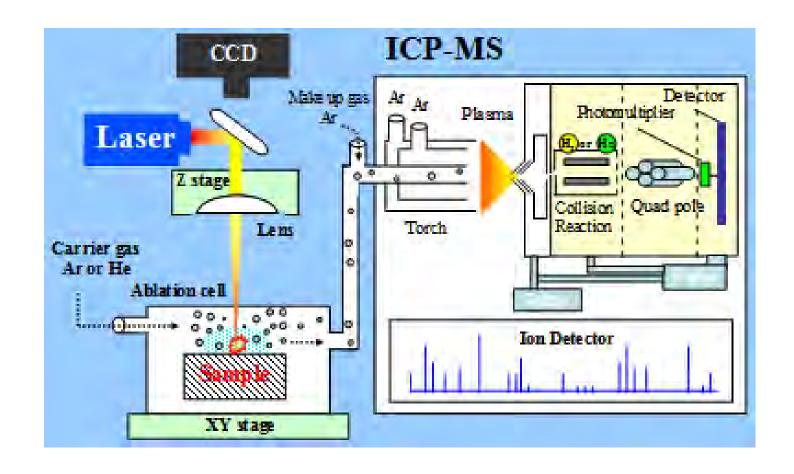
Secondary Ion Mass Spectrometry

Large variety of ionization sources and mass spectrometer types facilitate instrument configurations with unique performance capabilities

- Ultrahigh sensitivity to surface layers (TOF-SIMS)
- Detection limits in the low ppm/ppb range
- Elemental and molecular analysis
- Ultra-shallow depth profiles or depth profiles of tens of µm
- Imaging capabilities
- Retrospective analysis of raw data streams (TOF-SIMS)
- Universal applicability to practically all types of solid materials and sample forms









Methodology:

- •Dynamic secondary ion mass spectrometry (SIMS) analyses were performed using a Cameca IMS-3f SIMS instrument.
- •The SIMS analyses were performed using 400 nA, 5.5 keV Cs $^+$ primary ion beam that was rastered over a 250 x 250 μm^2 area on the specimen surface.
- •Negative secondary ions were collected from a 150 µm area within this sputtered area.
- •A micro-channel plate was employed for collecting the SIMS images.
- •SIMS images were collected for the mass number ²⁷BO after each sputter cycle.
- •Intensity of ²⁷BO was monitored instead of ¹¹B because of the intensity enhancement by the presence of oxygen improves the detection limit.
- •SIMS images have been presented on a thermal scale, i.e. brighter areas qualitatively represent the presence of greater amounts of the element of interest in that area.
- •The collected SIMS images were stacked together to create a three-dimensional image.



